	Туре	L #	Hits	S arch T xt	DBs	Time Stamp
1	BRS	L1	892	and day and	USPAT; EPO; JPO; DERWEN T; IBM_TD B	12:19
2	BRS	L2	293	438/460.ccls. and @ay<2000	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/02/11 12:20
3	BRS	L3	218	29/413.ccls. and @ay<2000	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/02/11 12:21
4	BRS	L4	13	3 and(chip wafer) and (dicing dice)	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/02/11 12:20
5	BRS	L5	4	29/417.ccls. and @ay<2000 and (chip wafer) and (dicing dice)	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/02/11 12:22
6	BRS	L6	4	29/418.ccls. and @ay<2000 and (chip wafer) and (dicing dice)	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/02/11 12:22

	Туре	L#	Hits	S arch Text	DBs	Time Stamp
7	BRS	L7	14421	(chip wafer) and (dicing dice)	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/02/11 12:23
8	BRS	L8	5978	7 and thin\$4	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/02/11 12:23
9	BRS	L 9	432	8 and foil	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/02/11 12:23
10	BRS	L10	6764	wafer and dicing and @ay<2000	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/02/11 12:24
11	BRS	L11	368	438/113.ccls. and @ay<2000	USPAT; EPO; JPO; DERWEN T; IBM_TD	2004/02/11 12:24
12	BRS	L12	0	wafer and (trench groove) and (intermediate adj support) and (adhesive adj foil) and (dry adj etch)	USPAT; EPO; JPO; DERWEN T; IBM_TD	2004/02/11 12:26

	Туре	L #	Hits	S arch Text	DBs	Time Stamp
13	BRS	L13	0	wafer and (trench groove) and (adhesive adj foil) and (dry adj etch) and thin\$4	USPAT; EPO; JPO; DERWEN T; IBM_TD B	
14	BRS	L14	1	wafer and (trench groove) and (adhesive adj foil) and thin\$4	USPAT; EPO; JPO; DERWEN T; IBM_TD B	
15	BRS	L15	20	wafer and (adhesive adj foil) and thin\$4	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/02/11 12:28
16	BRS	L16	0	15 and (dry adi etch)	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/02/11 12:29
17	BRS	L17	1604	(groove trench) and (dry adj etch) and @ay<2000	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/02/11 12:30
18	BRS	L18	38	17 and dice	USPAT; EPO; JPO; DERWEN T; IBM_TD B	12:30